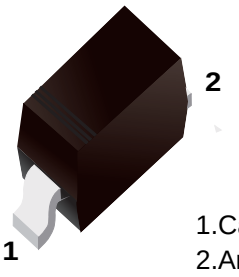
■Silicon Schottky Barrier Diode



1.Cathode
2.Anode

■ Simplified outline(SOD-123)

■ Features

- Metal silicon unction, maority carrier conduction
- Ideal for used in detection or for switching on the radio, TV, etc.

■ Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbols	1N60PW	Units
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Forward Current at V_F=1V	I_F	4	mA
Reverse Current at V_R=10V	I_R	50	uA
Total Capacitance at f=1MHz,V=-1V	C_{tot}	1	pF
Rectification efficiency at Vi = 2 V_{RMS}, R = 5 KΩ	η	55	%
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55 ~ +150	°C

Fig.1 Forward Characteristics

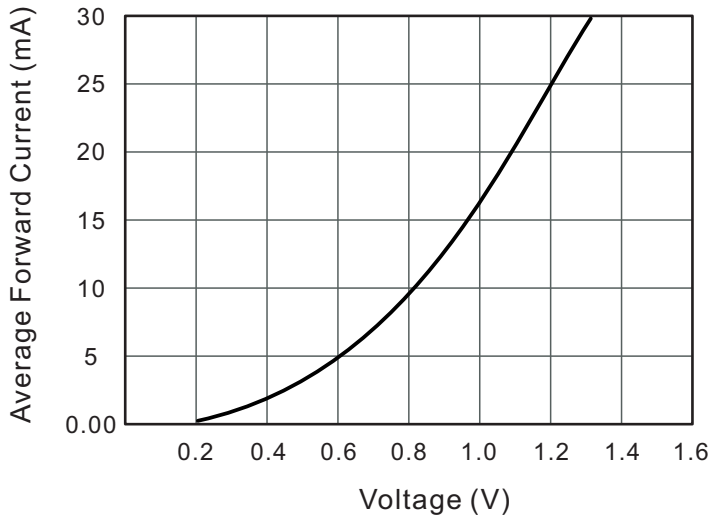
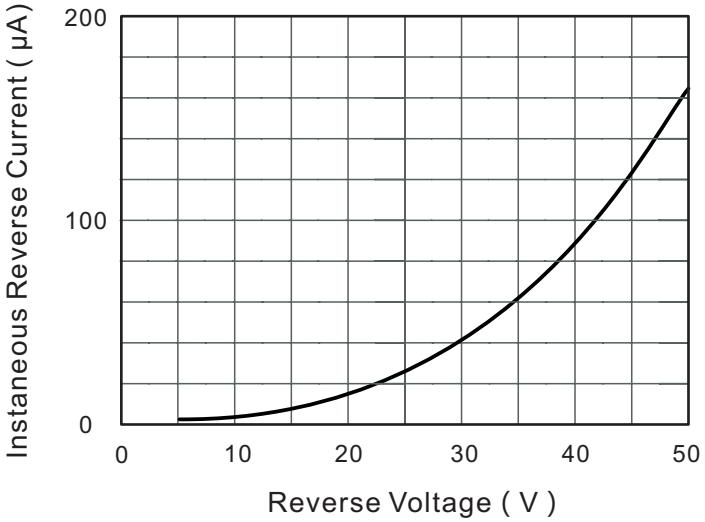
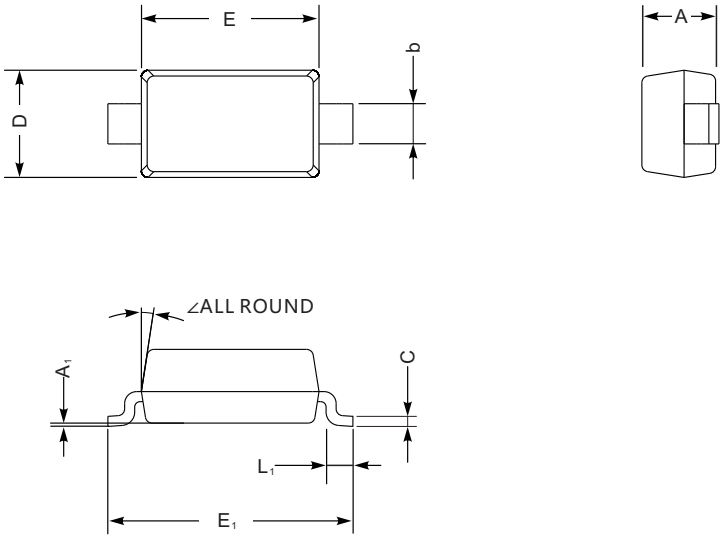


Fig.2 Typical Reverse Characteristics



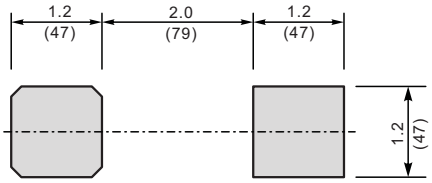
Package Outline SOD-123

Plastic surface mounted package; 2 leads



UNIT		A	C	D	E	E_1	L_1	b	A_1	∠
mm	max	1.3	0.22	1.8	2.8	3.9	0.45	0.7	0.2	9°
	min	0.9	0.09	1.5	2.5	3.6	0.25	0.5	—	
mil	max	51	8.7	71	110	154	18	28	8	
	min	35	3.5	59	98	142	10	20	—	

The recommended mounting pad size



Unit: mm (mil)

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOD-123	Tape/Reel,7"reel	3000	EIA-481-1